

BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

Darlington Complementary Silicon Power Transistors

These devices are designed for general purpose and low speed switching applications.

Features

- High DC Current Gain – $h_{FE} = 2500$ (typ.) at $I_C = 4.0$
- Collector-Emitter Sustaining Voltage at 100 mAdc
 $V_{CEO(sus)} = 80$ Vdc (min) – BDX33B, BDX34B
 $= 100$ Vdc (min) – BDX33C, BDX34C
- Low Collector-Emitter Saturation Voltage
 $V_{CE(sat)} = 2.5$ Vdc (max) at $I_C = 3.0$ Adc
– BDX33B, 33C/34B, 34C
- Monolithic Construction with Build-In Base-Emitter Shunt Resistors
- Pb-Free Packages are Available*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|----------------|-------------|--------------------------|
| Collector-Emitter Voltage BDX33B, BDX34B BDX33C, BDX34C | V_{CEO} | 80 100 | Vdc |
| Collector-Base Voltage BDX33B, BDX34B BDX33C, BDX34C | V_{CB} | 80 100 | Vdc |
| Emitter-Base Voltage | V_{EB} | 5.0 | Vdc |
| Collector Current – Continuous – Peak | I_C | 10 15 | Adc |
| Base Current | I_B | 0.25 | Adc |
| Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C | P_D | 70 0.56 | W W/ $^\circ\text{C}$ |
| Operating and Storage Junction Temperature Range | T_J, T_{stg} | -65 to +150 | $^\circ\text{C}$ |

THERMAL CHARACTERISTICS

| Characteristics | Symbol | Max | Unit |
|--------------------------------------|-----------------|------|--------------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 1.78 | $^\circ\text{C/W}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

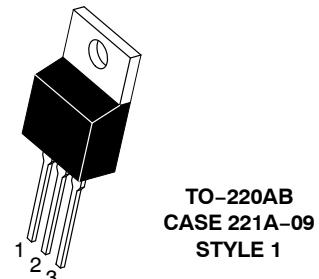
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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**DARLINGTON
10 AMPERE
COMPLEMENTARY SILICON
POWER TRANSISTORS
80–100 VOLTS, 65 WATTS**



MARKING DIAGRAM



$BDX3xy$ = Device Code
 $x = 3$ or 4
 $y = B$ or C
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

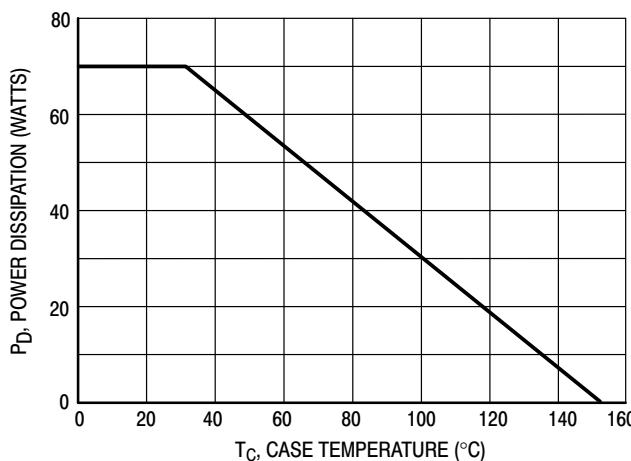


Figure 1. Power Derating

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|--|------------------------------|-----------|------------|-----------------------|
| OFF CHARACTERISTICS | | | | |
| Collector-Emitter Sustaining Voltage (Note 1) ($I_C = 100 \text{ mA}_\text{dc}$, $I_B = 0$) | $V_{\text{CEO}(\text{sus})}$ | 80 100 | — | Vdc |
| Collector-Emitter Sustaining Voltage (Note 1) ($I_C = 100 \text{ mA}_\text{dc}$, $I_B = 0$, $R_{BE} = 100$) | $V_{\text{CER}(\text{sus})}$ | 80 100 | — | Vdc |
| Collector-Emitter Sustaining Voltage (Note 1) ($I_C = 100 \text{ mA}_\text{dc}$, $I_B = 0$, $V_{BE} = 1.5 \text{ Vdc}$) | $V_{\text{CEX}(\text{sus})}$ | 80 100 | — | Vdc |
| Collector Cutoff Current ($V_{CE} = 1/2$ rated V_{CEO} , $I_B = 0$) | I_{CEO} | — — | 0.5 10 | mA_dc |
| Collector Cutoff Current ($V_{CB} = \text{rated } V_{\text{CBO}}$, $I_E = 0$) | I_{CBO} | — — | 1.0 5.0 | mA_dc |
| Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}$, $I_C = 0$) | I_{EBO} | — | 10 | mA_dc |

ON CHARACTERISTICS

| | | | | |
|--|-----------------------------|-----|-----|-----|
| DC Current Gain (Note 1) ($I_C = 3.0 \text{ Adc}$, $V_{CE} = 3.0 \text{ Vdc}$) | h_{FE} | 750 | — | — |
| Collector-Emitter Saturation Voltage ($I_C = 3.0 \text{ Adc}$, $I_B = 6.0 \text{ mA}_\text{dc}$) | $V_{\text{CE}(\text{sat})}$ | — | 2.5 | Vdc |
| Base-Emitter On Voltage ($I_C = 3.0 \text{ Adc}$, $V_{CE} = 3.0 \text{ Vdc}$) | $V_{\text{BE}(\text{on})}$ | — | 2.5 | Vdc |
| Diode Forward Voltage ($I_C = 8.0 \text{ Adc}$) | V_F | — | 4.0 | Vdc |

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.
2. Pulse Test non repetitive: Pulse Width = 0.25 seconds.

BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

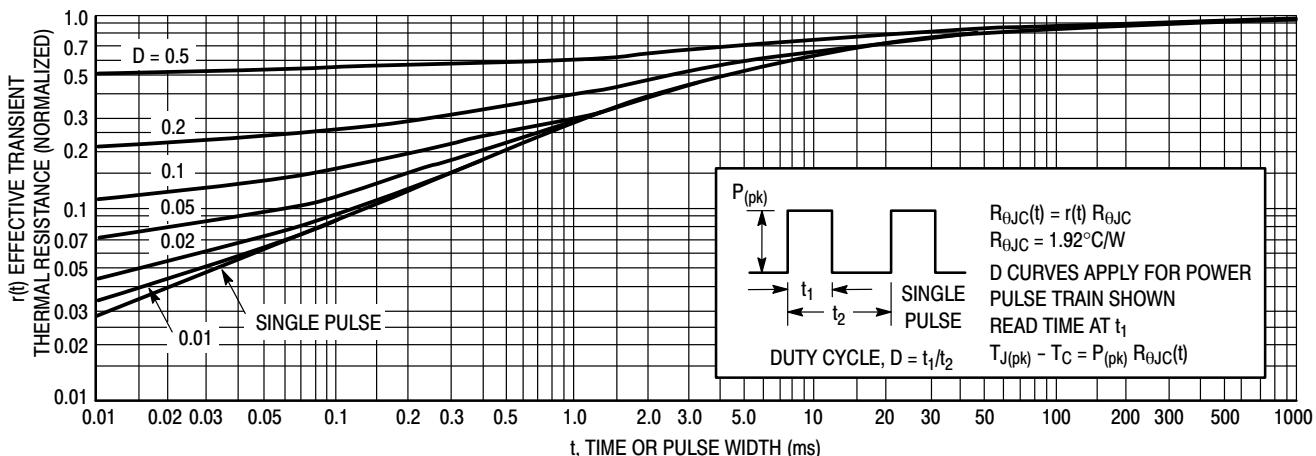


Figure 1. Thermal Response

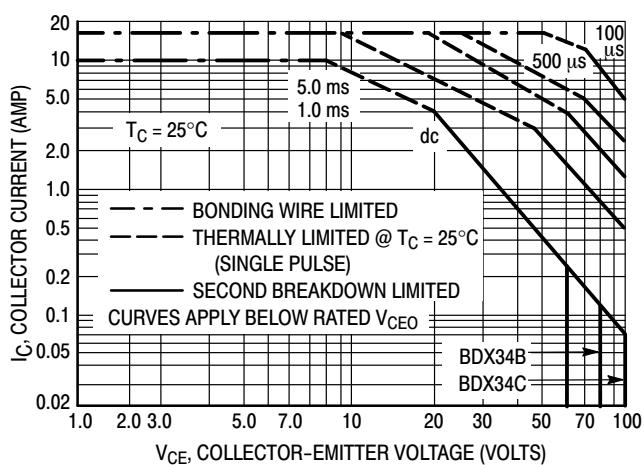
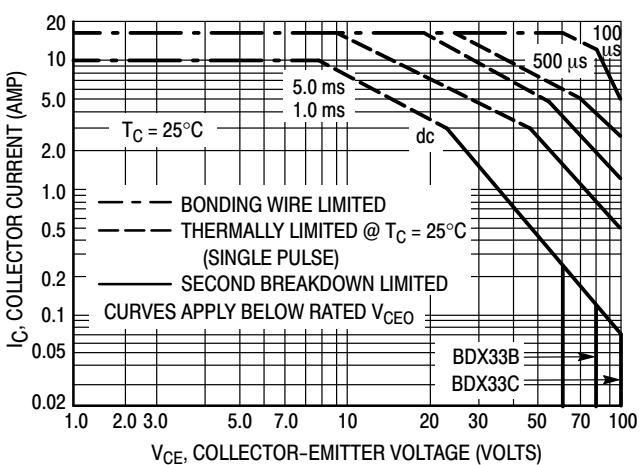


Figure 2. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 3 is based on $T_{J(pk)}$



$= 150^{\circ}\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} = 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

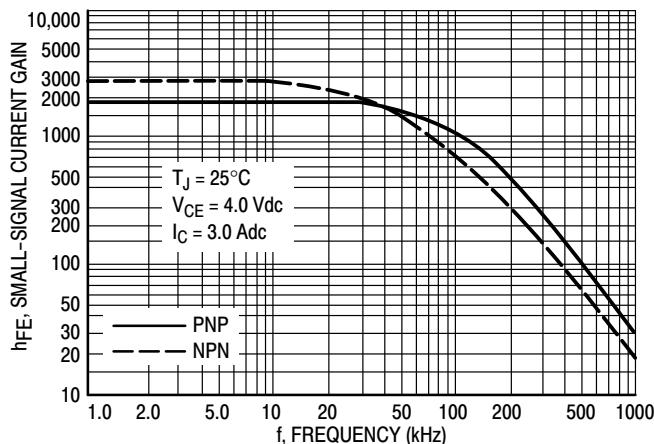


Figure 3. Small-Signal Current Gain

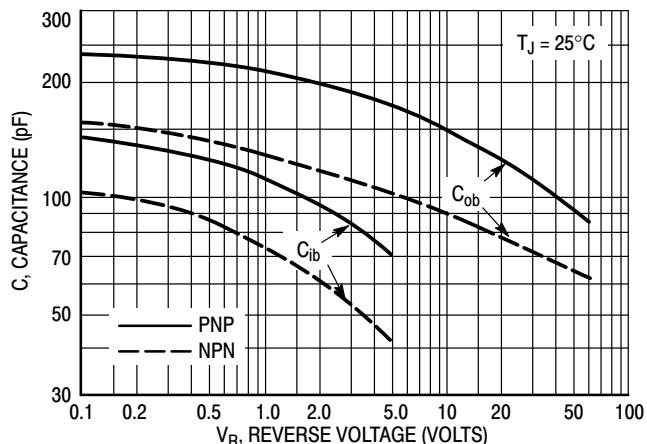


Figure 4. Capacitance

BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

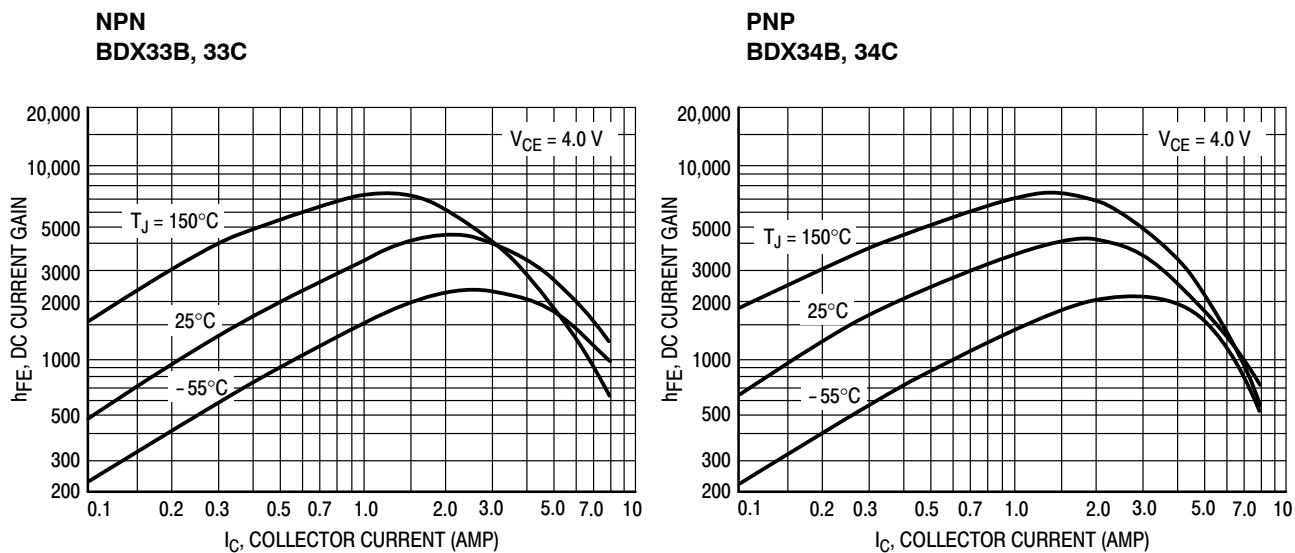


Figure 5. DC Current Gain

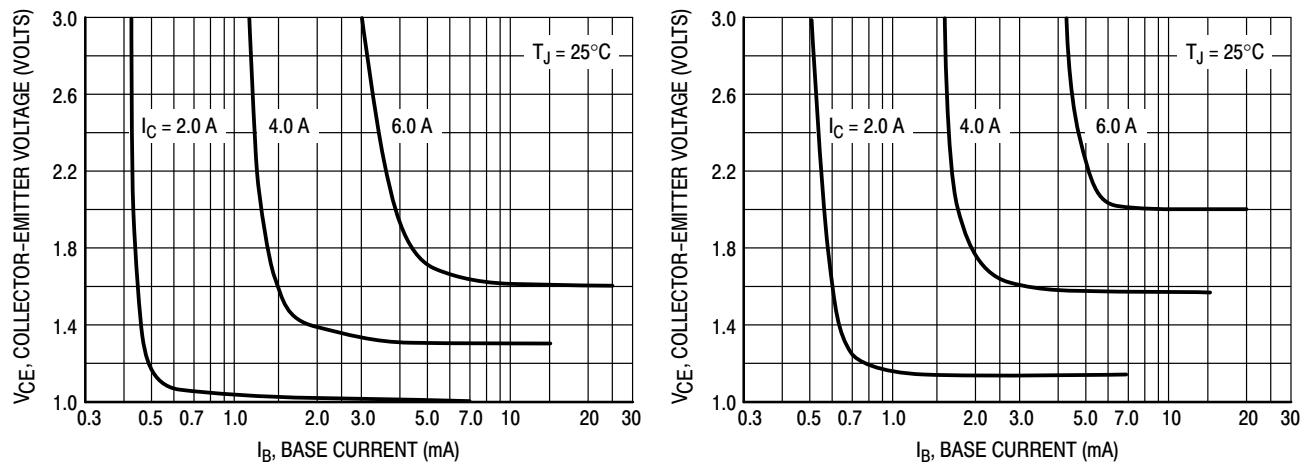


Figure 6. Collector Saturation Region

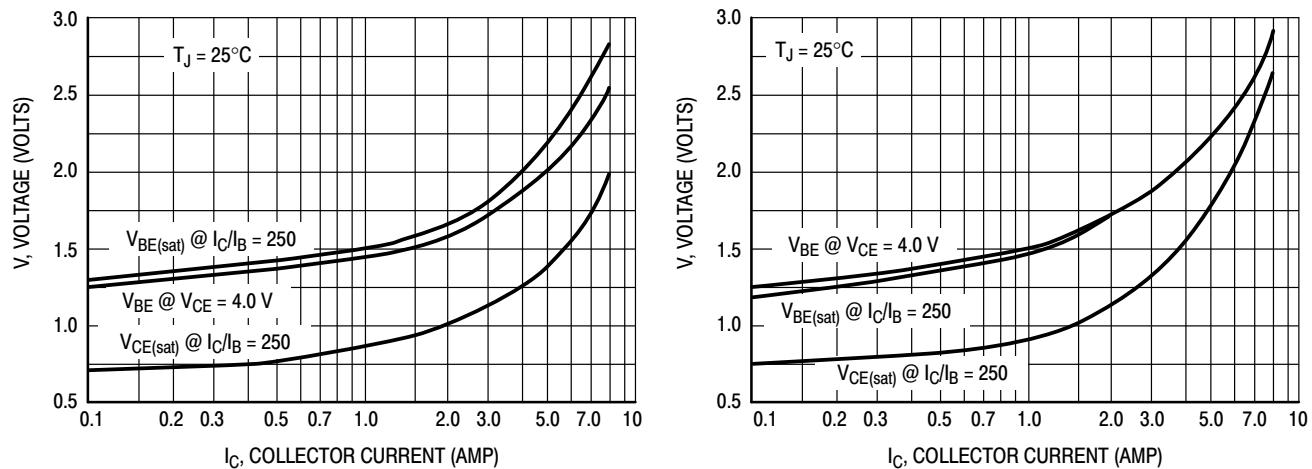


Figure 7. "On" Voltages

BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

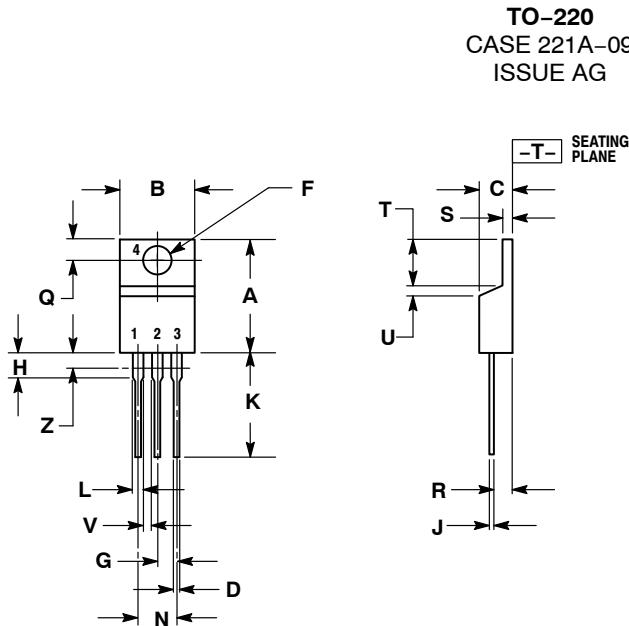
ORDERING INFORMATION

| Device | Package | Shipping[†] |
|---------------|---------------------|-----------------------------|
| BDX33B | TO-220 | 50 Units / Rail |
| BDX33BG | TO-220 (Pb-Free) | |
| BDX33C | TO-220 | 50 Units / Rail |
| BDX33CG | TO-220 (Pb-Free) | |
| BDX34B | TO-220 | 50 Units / Rail |
| BDX34BG | TO-220 (Pb-Free) | |
| BDX34C | TO-220 | 50 Units / Rail |
| BDX34CG | TO-220 (Pb-Free) | |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BDX33B, BDX33C (NPN) BDX34B, BDX34C (PNP)

PACKAGE DIMENSIONS



TO-220
CASE 221A-09
ISSUE AG

NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.405 | 9.66 | 10.28 |
| C | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.036 | 0.64 | 0.91 |
| F | 0.142 | 0.161 | 3.61 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.161 | 2.80 | 4.10 |
| J | 0.014 | 0.025 | 0.36 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

- STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. Emitter
 4. COLLECTOR

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